

DESCRIPTIVE ABSTRACT

The invention relates to the field of
fabrication methods in thin layers, for example of
5 integrated electronic circuits or MEMS.

It relates to a correction method allowing
design errors made for example by photolithography in a
thin layer to be repaired, and without necessarily
having to utilise a new mask or without having to
10 correct an erroneous mask. The invention likewise
comprises a lithography device allowing certain of the
steps of such a method to be employed.

Figure 3A.

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